

ABSTRACT OF THE DISCLOSURE

A plasma film-forming apparatus which includes a film-forming chamber in which a substrate is arranged, a film-forming gas introducing pipe is connected to a supply source of a film-forming gas at its first end, a shower plate having numerous holes through which a second end of the film-forming gas introducing pipe communicates with the film-forming chamber, film-gas exciting means for exciting film-forming gas introduced through the shower plate into the film-forming chamber to form a film on the surface of the substrate with the chemical reaction, radicals-producing means which excites the cleaning gas and produces radicals, and cleaning-gas introducing means which introduces the cleaning gas containing the radicals into the film-forming chamber. The apparatus is improved by the cleaning-gas introducing means communicating directly with the film-forming chamber.

100-110-120-130-140-150-160-170-180-190